

TLE94108EL

Features

- Eight half bridge power outputs
- Very low power consumption in sleep mode
- 3.3V / 5V compatible inputs with hysteresis
- All outputs with overload and short circuit protection
- Independently diagnosable outputs (overcurrent, open load)
- Open load diagnostics in ON-state for all high-side and low-side
- Outputs with selectable open load thresholds (HS1, HS2)
- 16-bit Standard SPI interface with daisy chain and in-frame response capability for control and diagnosis
- Fast diagnosis with the global error flag
- PWM capable outputs for frequencies 80Hz, 100Hz and 200Hz with 8-bit duty cycle resolution
- Overtemperature pre-warning and protection
- Over- and Undervoltage lockout
- Cross-current protection

Applications

- HVAC Flap DC motors
- Monostable and bistable Relays
- Side mirror x-y adjustment and mirror fold
- LEDs

Description

The TLE94108EL is a protected eight-fold half-bridge driver designed especially for automotive motion control applications such as Heating, Ventilation and Air Conditioning (HVAC) flap DC motor control. It is part of a larger family offering half-bridge drivers from three outputs to twelve outputs with direct interface or SPI interface.

The half bridge drivers are designed to drive DC motor loads in sequential or parallel operation. Operation modes forward (cw), reverse (ccw), brake and high impedance are controlled from a 16-bit SPI interface. It offers diagnosis features such as short circuit, open load, power supply failure and overtemperature detection. In combination with its low quiescent current, this device is attractive among others for automotive applications. The small fine pitch exposed pad package, PG-SSOP-24, provides good thermal performance and reduces PCB-board space and costs.

Table 1 Product Summary

Table of Contents

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TLE94108EL

Pin Configuration

1 Pin Configuration

1.1 Pin Assignment

1.2 Pin Definitions and Functions

Pin Configuration

 $\overline{1}$) The exposed die pad at the bottom of the package allows better heat dissipation from the device via the PCB. The exposed pad (EP) must be either left open or connected to GND. It is recommended to connect EP to GND for best EMC and thermal performance.

Note: Not used (N.U.) pins and unused outputs are recommended to be left unconnected (open) on the application board. If N.U. pins or unused output pins are routed to an external connector which leaves the PCB, then these outputs should have provision for a zero ohm jumper (depopulated if unused) or ESD protection. In other words, they should be treated like used pins.

Block Diagram

2 Block Diagram

Figure 2 Block Diagram TLE94108EL (SPI Interface)

Block Diagram

2.1 Voltage and current definition

[Figure 3](#page-7-1) shows terms used in this datasheet, with associated convention for positive values.

3 General Product Characteristics

3.1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings1)*T***^j = -40°C to +150°C**

1) Not subject to production test, specified by design

2) Also applicable to not used (N.U.) pins

3) ESD susceptibility, "JEDEC HBM" according to ANSI/ ESDA/ JEDEC JS001 (1.5 kΩ, 100pF)

4) ESD susceptibility, Charged Device Model "CDM" according JEDEC JESD22-C101

TLE94108EL

General Product Characteristics

Notes

- *1. Stresses above the ones listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*
- *2. Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.*

3.2 Functional Range

Table 3 Functional Range

1) Not subject to production test, specified by design.

2) In the extended supply range, the device is still functional. However, deviations of the specified electrical characteristics are possible.

Note: Within the normal functional range the IC operates as described in the circuit description. The electrical characteristics are specified within the conditions given in the related electrical characteristics table.

3.3 Thermal Resistance

Table 4 Thermal Resistance TLE94108EL

1) Not subject to production test, specified by design.

2) Specified R_{thJA} value is according to JEDEC JESD51-2, -3 at natural convection on FR4 1s0p board; The product (chip + package) was simulated on a 76.2 x 114.3 x 1.5mm board with minimal footprint copper area and 35µm thickness. Ta = -40°C, each channel dissipates 0.2W. Ta = 85°C, each channel dissipates 0.135W.

- 3) Specified R_{thJA} value is according to JEDEC JESD51-2, -3 at natural convection on FR4 1s0p board; The product (chip + package) was simulated on a 76.2 x 114.3 x 1.5mm board with additional cooling of 300mm2 copper area and 35µm thickness. Ta = -40°C, each channel dissipates 0.2W. Ta = 85°C, each channel dissipates 0.135W.
- 4) Specified $R_{th,IA}$ value is according to JEDEC JESD51-2, -3 at natural convection on FR4 1s0p board; The product (chip + package) was simulated on a 76.2 x 114.3 x 1.5mm board with additional cooling of 600mm2 copper area and 35µm thickness. Ta = -40°C, each channel dissipates 0.2W. Ta = 85°C, each channel dissipates 0.135W.
- 5) Specified R_{th JA} value is according to JEDEC JESD51-2, -3 at natural convection on FR4 2s2p board; The product (chip + package) was simulated on a 76.2 x 114.3 x 1.5mm board with two inner copper layers (4 x 35µm Cu). Ta = -40°C, each channel dissipates 0.2W. Ta = 85°C, each channel dissipates 0.135W.

3.4 Electrical Characteristics

<code>Table 5 Electrical Characteristics, V_{S} =5.5 V to 18 V, V_{DD} = 3.0V to 5.5V, T_{j} = -40°C to +150°C, EN= HIGH,</code> V_{OUTD} = 0 A; Typical values refer to V_{DD} = 5.0 V, V_{S} = 13.5 V and T_{J} = 25 °C unless otherwise **specified; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)**

<code>Table 5 Electrical Characteristics, $V_{\sf s}$ =5.5 V to 18 V, $V_{\sf DD}$ = 3.0V to 5.5V, $T_{\sf j}$ = -40°C to +150°C, EN= HIGH,</code> V_{OUTD} = 0 A; Typical values refer to V_{DD} = 5.0 V, V_{S} = 13.5 V and T_{J} = 25 °C unless otherwise **specified; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)** (cont'd)

Parameter	Symbol	Values			Unit	Note or	Number
		Min.	Typ.	Max.		Test Condition	
High-Side R _{DSON} (HS1 and HS2 in LED mode)	$R_{\text{DSON_HI_HB}}$ 25C		950	1300	$m\Omega$	²⁾ I_{OUT} = ±0.1 A; $T_i = 25 °C$	$P_4.4.18$
High-Side R _{DSON} (HS1 and HS2 in LED mode)	$R_{\text{DSON_HI_HB}_-}$ 150C		1500	2000	$m\Omega$	²⁾ $I_{\text{OUT}} = \pm 0.1 \text{ A};$ $T_i = 150 °C$	$P_4.4.19$
Output Protection and Diagnosis of high-side (HS) channels of half-bridge output							
HS Overcurrent Shutdown Threshold	I_{SD_HS}	-1.4	-1.1	-0.9	A	See Figure 7	P_4.4.89
Difference between shutdown and limit current	I_{LIM_HS} - I_{SD_HS}	-1.2	-0.6	$\mathbf 0$	$\mathsf A$	³⁾ $ I_{LIM_HS} \geq I_{SD_HS} $ See Figure 7	$P_4.4.21$
Overcurrent Shutdown filter time	$t_{\text{dSD_HS}}$	15	19	23	μs	3)	$P_4.4.22$
Open Load Detection Current	$I_{\text{OLD1_HS}}$	-15	-8	-3	mA	\overline{a}	$P_4.4.23$
Open Load Detection filter time	$t_{\text{OLD1_HS}}$	2000	3000	4000	μs	3)	$P_4.4.24$
Open Load Detection Current for LED mode (HS1 & HS2)	$I_{\text{OLD2_HS1,2}}$	-3.2	-2	-0.5	mA	Bit OL_SEL_HS1 = $1, 0L$ _SEL_HS2 = 1	$P_4.4.25$
Open Load Detection filter time for LED mode (HS1 & HS2)	$t_{\text{OLD2_HS1,2}}$	100	200	300	μs	Bit OL_SEL_HS1 = $1, 0L$ _SEL_HS2 = 1; 3)	$P_4.4.26$
Output Protection and Diagnosis of low-side (LS) channels of half-bridge output							
LS Overcurrent Shutdown Threshold	$I_{SD \perp S}$	0.9	1.1	1.4	A	Figure 8	P_4.4.104
Difference between shutdown and limit current	I_{LIM_LS} - I_{SD_LS}	0	0.6	1.2	$\mathsf A$	³⁾ $I_{LIM_LS} \geq I_{SD_LS}$ Figure 8	$P_4.4.28$
Overcurrent Shutdown filter time	t_{dSD_LS}	15	19	23	μs	3)	$P_4.4.29$
Open Load Detection Current	I_{OLD_LS}	3	8	15	mA		$P_4.4.30$
Open Load Detection filter time	t_{OLD_LS}	2000	3000	4000	μs	3)	$P_4.4.31$
Outputs OUT(1n) leakage current							
HS leakage current in off state	I _{QLHn_NOR}	-2	-0.5	$\qquad \qquad -$	μA	$V_{\text{OUTD}} = \text{OV}$; EN=High P_4.4.32	
HS leakage current in off state	I _{QLHn_SLE}	-2	-0.5	$\overline{}$	μA	$V_{\text{OUTn}} = \text{OV}$; EN=GND	$P_4.4.33$
LS Leakage current in off state	I _{QLLn_NOR}	$\overline{}$	0.5	$\mathbf 2$	μA	$V_{\text{OUTn}} = V_{\text{S}}$; EN=High P_4.4.34	
LS Leakage current in off state	IQLLn_SLE		0.5	$\overline{2}$	μA	$V_{\text{OUTD}} = V_{\text{S}}$; EN=GND	$P_4.4.35$
Output Switching Times. See Figure 9 and Figure 10.							
Slew rate of high-side and low- side outputs	d_{VOUT}/dt	0.1	0.45	0.75	$V/\mu s$	Resistive load = 100Ω; V_S =13.5V ⁴⁾	P_4.4.36

<code>Table 5 Electrical Characteristics, $V_{\sf s}$ =5.5 V to 18 V, $V_{\sf DD}$ = 3.0V to 5.5V, $T_{\sf j}$ = -40°C to +150°C, EN= HIGH,</code> V_{OUTD} = 0 A; Typical values refer to V_{DD} = 5.0 V, V_{S} = 13.5 V and T_{J} = 25 °C unless otherwise **specified; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)** (cont'd)

Parameter	Symbol	Values			Unit	Note or	Number
		Min.	Typ.	Max.		Test Condition	
Output delay time high side driver on	t_{dONH}	5	20	35	μs	Resistive load = 100Ω to GND	P_4.4.37
Output delay time high side driver off	t_{dOFFH}	15	45	75	μs	Resistive load = 100Ω to GND	P_4.4.38
Output delay time low side driver on	t_{donL}	5	20	35	μs	Resistive load = 100Ω to VS	P_4.4.39
Output delay time low side driver off	$t_{\sf doFFL}$	15	45	75	μs	Resistive load = 100Ω to VS	$P_4.4.40$
Cross current protection time, high to low	t_{DHL}	100	130	160	μs	Resistive load = $100\Omega^{3}$	$P_4.4.41$
Cross current protection time, low to high	t_{DLH}	100	130	160	μs	Resistive load = $100\Omega^{3}$	$P_4.4.42$
Input Interface: Logic Input EN							
High-input voltage	V_{ENH}	$0.7*$ V_{DD}		$\qquad \qquad -$	$\sf V$		$P_4.4.43$
Low-input voltage	V_{ENL}		$\overline{}$	$0.3*$ V_{DD}	V	$\overline{}$	$P_4.4.44$
Hysteresis of input voltage	V_{ENHY}	$\overline{}$	500	$\overline{}$	mV	3)	$P_4.4.45$
Pull down resistor	$R_{\text{PD_EN}}$	20	40	70	kΩ	V_{FN} = 0.2 x V_{DD}	$P_4.4.46$
SPI frequency							
Maximum SPI frequency	$f_{\rm SPI,max}$			5.0	MHz	3) 5)	P_4.4.47
SPI INTERFACE: Delay Time from EN rising edge to first Data in							
Setup time	t_{set}			150	μs	$3)$ See Figure 14	$P_4.4.48$
SPI INTERFACE: Input Interface, Logic Inputs SDI, SCLK, CSN							
H-input voltage threshold	$V_{\rm IH}$	$0.7 *$ V_{DD}			V		$P_4.4.50$
L-input voltage threshold	V_{IL}			$0.3 *$ V_{DD}	$\sf V$		$P_4.4.51$
Hysteresis of input voltage	V_{IHY}	$\overline{}$	500	$\qquad \qquad -$	mV	3)	$P_4.4.52$
Pull up resistor at pin CSN	$R_{\rm PU_CSN}$	30	50	80	kΩ	$V_{CSN} = 0.7 \times V_{DD}$	$P_4.4.53$
Pull down resistor at pin SDI, SCLK	$R_{\rm PD_SDI}$ $R_{\text{PD_SCLK}}$	20	40	70	kΩ	V_{SDI} , $V_{SCLR} = 0.2 \times V_{DD}$	$P_4.4.54$
Input capacitance at pin CSN, SDI or SCLK	C_{1}	$\overline{}$	10	15	pF	$0V < V_{DD}$ < 5.25V ³⁾	$P_4.4.55$
Input Interface, Logic Output SDO							
H-output voltage level	V_{SDOH}	V_{DD} - 0.4	V_{DD} - 0.2		V	I_{SDOH} = -1.6 mA	$P_4.4.56$

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<code>Table 5 Electrical Characteristics, $V_{\sf s}$ =5.5 V to 18 V, $V_{\sf DD}$ = 3.0V to 5.5V, $T_{\sf j}$ = -40°C to +150°C, EN= HIGH,</code> V_{OUTD} = 0 A; Typical values refer to V_{DD} = 5.0 V, V_{S} = 13.5 V and T_{J} = 25 °C unless otherwise **specified; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)** (cont'd)

Parameter	Symbol	Values			Unit	Note or	Number
		Min.	Typ.	Max.		Test Condition	
SDO Valid Time for V_{DD} = 5V	ι VASDO5		50	65	ns	V_{SDO} < 0.2 x V_{DD} V_{SDO} > 0.8 V_{DD} C _{load} = 40pF ³⁾	P 4.4.79

Thermal warning & Shutdown

1) $I_{S_{HSON}}$ does not include the load current

2) HS1, respectively HS2, is set to LED mode by setting OL_SEL_HS1 bit to 1, respectively OL_SEL_HS2 bit to 1

3) Not subject to production test, specified by design

4) Measured for 20% - 80% of V_s .

5) Not applicable in daisy chain configuration

Characterization results

4 Characterization results

Performed on 7 devices from 2 lots, over operating temperature and nominal/extended supply range.

Typical performance characteristics

Supply quiescent current Supply current Supply current

Logic supply quiescent current **Logic supply current**

HS static Drain-source ON-resistance LS static Drain-source ON-resistance

HS static drain-source ON-resistance VS = 13.5V and VDD = 5V

600 700 800 900 1000 1100 1200 **Ω]** 1300 1400 1500 1600 -50 -30 -10 10 30 50 70 90 110 130 150 **RDSON_LS [m Junction Temperature [°C] P_4.4.16 and P_4.4.17** $-VS=5.5V$ $-VS=13.5V$ $-VS=18V$ $-VS=19V$ $-VS=21V$

LS static drain-source ON-resistance VS = 13.5V and VDD = 5V

Slew rate ON of high-side outputs Slew rate ON of low-side outputs

Slew rate OFF of high-side outputs Slew rate OFF of low-side outputs

0.2 0.25 0.3 0.35 0.4 0.45 0.5 0.55 0.6 0.65 -50 -30 -10 10 30 50 70 90 110 130 150 **dVOUT/ dt [V/us] Junction Temperature [°C] P_4.4.36** $-VS=5.5V$ $-VS=13.5V$ $-VS=18V$ $-VS=19V$ $-VS=21V$

HS overcurrent shutdown threshold LS overcurrent shutdown threshold

Undervoltage switch ON voltage threshold Undervoltage switch OFF voltage threshold

Overvoltage switch ON voltage threshold Overvoltage switch OFF voltage threshold

VDD Power-on-reset and VDD Power-off-reset

General Description

5 General Description

5.1 Power Supply

The TLE94108EL has two power supply inputs, V_S and V_{DD} . The half bridge outputs are supplied by V_S , which is connected to the 12V automotive supply rail. *V*_{DD} is used to supply the I/O buffers and internal voltage regulator of the device.

 V_S and V_{DD} supplies are separated so that information stored in the logic block remains intact in the event of voltage drop outs or disturbances on V_s . The system can therefore continue to operate once V_s has recovered, without having to resend commands to the device.

A rising edge on *V*_{DD} crossing *V*_{DD POR} triggers an internal Power-On Reset (POR) to initialize the IC at power-on. All data stored internally is deleted, and the outputs are switched off (high impedance).

An electrolytic and 100nF ceramic capacitors are recommended to be placed as close as possible to the V_S supply pin of the device for improved EMC performance in the high and low frequency band. The electrolytic capacitor must be dimensioned to prevent the VS voltage from exceeding the absolute maximum rating. In addition, decoupling capacitors are recommended on the *V*_{DD} supply pin.

5.2 Operation modes

5.2.1 Normal mode

The TLE94108EL enters normal mode by setting the EN input High. In normal mode, the charge pump is active and all output transistors can be configured via SPI.

5.2.2 Sleep mode

The TLE94108EL enters sleep mode by setting the EN input Low. The EN input has an internal pull-down resistor.

In sleep mode, all output transistors are turned off and the SPI register banks are reset. The current consumption is reduced to $I_{SQ} + I_{DD_Q}$.

5.3 Reset Behaviour

The following reset triggers have been implemented in the TLE94108EL:

V_{DD} Undervoltage Reset:

The SPI Interface shall not function if V_{DD} is below the undervoltage threshold, $V_{DD\ POHR}$. The digital block will be deactivated, the logic contents cleared and the output stages are switched off . The digital block is initialized once V_{DD} voltage levels is above the undervoltage threshold, V_{DD POR}. Then the NPOR bit is reset (NPOR = 0 in **[SYS_DIAG1](#page-63-1)** and Global Status Register).

Reset on EN pin:

If the EN pin is pulled Low, the logic content is reset and the device enters sleep mode.

The reset event is reported by the NPOR bit (NPOR = 0) once the TLE94108EL is in normal mode (EN = High; VDD $> V_{DD POR}$).

General Description

5.4 Reverse Polarity Protection

The TLE94108EL requires an external reverse polarity protection. During reverse polarity, the free-wheeling diodes across the half bridge output will begin to conduct, causing an undesired current flow (/_{RB}) from ground potential to battery and excessive power dissipation across the diodes. As such, a reverse polarity protection diode is recommended (see **[Figure 4](#page-23-1)**).

Figure 4 Reverse Polarity Protection

6 Half-Bridge Outputs

6.1 Functional Description

The half-bridge outputs of the TLE94108EL are intended to drive motor loads. These outputs can either be driven continuously or PWM enabled via SPI.

If the outputs are driven continuously via SPI, for example HS1 and LS2 used to drive a motor, then the following suggested SPI commands shall be sent:

- Activate HS1: Bit HB1_HS_EN in HB_ACT_1_CTRL register
- Activate LS2: Bit HB2_LS_EN in HB_ACT_1_CTRL register

6.1.1 Half-bridge operation with PWM enabled

All half-bridge outputs of the TLE94108EL are capable of PWM operation. They can either be used to drive an inductive load (e.g. DC brush motor) or optionally a resistive load (e.g. LED). Each half-bridge output has been allocated a maximum of three PWM channels with individual duty cycle settings with 8-bit resolution. Each channel is further mapped to a maximum of three PWM frequency options, i.e. 80Hz,100Hz and 200Hz. This feature enables a highly flexible PWM operation while driving loads with varying control profiles.

PWM frequency and duty cycle can be changed on demand during PWM operation of the desired half-bridge output. Glitches on the PWM output waveform, which may arise as a result of on-demand changes in PWM operation, will be prevented by the internal logic circuitry.

When operating with motor loads, active or passive free-wheeling configuration is available via SPI to select the speed at which the inductive current can decay over the full-bridge circuit. The default setting is passive free-wheeling.

Note: Active free-wheeling is effectively applied if the selected duty cycle corresponds to turn-on times of the HS and the LS, which are longer than the sum of the cross conduction times tDHL + tDLH.

6.1.1.1 Inductive Load

An illustration is shown in **[Figure 5](#page-25-1)** with OUT1 and OUT2 driving a DC brush motor. With this configuration, HS1 is permanently driven while LS2 is driven in PWM operation. HS2 serves to actively free-wheel (FW) the motor current load, reducing the power dissipation of the device.

Figure 5 PWM operation on OUT 2

Assuming HBx Mode = 00 and both HSx and LSx are considered off (tri-state). The suggested SPI control commands for proper PWM operation are:

Option 1: The considered output is not put in parallel with another one

- Configure the frequency to 00 (PWM is stopped and off) for selected PWM channel
- Configure active or passive free-wheeling of the inductive decay current in FW_CTRL register
- Assign an appropriate PWM channel for selected half-bridge output in HB_MODE_CTRL register
- Configure the duty cycle of the selected half-bridge output in PWM_DC_CTRL register
- Select the PWM frequency in PWM_CH_FREQ_CTRL register to begin the PWM period
- Activate the channel to be driven in PWM operation: HSn or LSn in the HB_ACT_CTRL register

Option 2: Outputs controlled by different control registers are put paralleled. This sequence ensures that corresponding HS or LS are activated simultaneously

- Configure the frequency 00 (PWM is stopped and off) for selected PWM channel
- Configure active or passive free-wheeling of the inductive decay current in FW_CTRL register
- Assign an appropriate PWM channel for selected half-bridge output in HB_MODE_CTRL register
- Configure the duty cycle of the selected half-bridge output in PWM_DC_CTRL register
- Activate the channel to be driven in PWM operation: HSn or LSn in the HB_ACT_CTRL register
- Select the PWM frequency in PWM_CH_FREQ_CTRL register to begin the PWM period

Careful attention should be paid to the free-wheeling configuration of the half-bridge required to be driven in PWM operation. For example, in the event a high-side channel is activated and assigned a PWM channel, and active free-wheeling is selected, but a frequency mode of '00' (PWM is stopped and off) is configured in the

PWM_CH_FREQ_CTRL register, then the respective high-side channel will be configured low and the adjacent low-side channel within the half-bridge will be enabled. This is a result of enabling active free-wheeling.

6.1.1.2 LED mode (optional)

Outputs, OUT1 and OUT2, are designed to optionally drive low current loads such as LEDs. The high-side channels, HS1 and HS2 are equipped with a lower open load threshold detection current and shorter filter time, specifically for low current loads such as LEDs. See OL_SEL_HS1 and OL_SEL_HS2 bits in FW_OL_CTRL register. Setting HS1 or HS2 in LED mode increases the R_{DSON} and decreases the open load detection threshold. An illustration is shown in **[Figure 6](#page-27-1)** with OUT1 driving an LED. With this configuration, HS1 is driven in PWM operation while LS1 is deactivated.

Figure 6 PWM operation on OUT 1

Assuming HBx Mode = 00 and both HSx and LSx are considered off (tri-state). The suggested SPI control commands are:

- Configure frequency 00 (PWM is stopped and off) for selected channel to ensure PWM is off.
- Assign an appropriate PWM channel for selected HS1 or HS2 output in HB_MODE_CTRL register
- Configure duty cycle of selected HS1 or HS2 output in PWM_DC_CTRL register
- Activate channel to be driven in PWM operation: HS1 or HS2 in the HB_ACT_CTRL register
- Select low current open load detection threshold for HS1 or HS2 in FW_OL_CTRL register
- Select PWM frequency in PWM_CH_FREQ_CTRL register to begin the PWM period.

6.2 Protection & Diagnosis

The TLE94108EL is equipped with an SPI interface to control and diagnose the state of the half-bridge drivers. This device has embedded protective functions which are designed to prevent IC destruction under fault conditions described in the following sections. Fault conditions are treated as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

The following table provides a summary of fault conditions, protection mechanisms and recovery states embedded in the TLE94108EL device.

Fault condition	Error Flag (EF) behaviour	Error bit: Status Register	Output Protection mechanism	Output error state	Output and error flag (EF) recovery
Overcurrent	Latch	1. Load Error bit, LE (bit 6) in SYS_DIAG 1: Global Status 1 Register 2. Localized error for each HS and LS channel of half-bridge, HBn_HS_OC and HBn_LS_OC bits in SYS_DIAG_2, SYS_DIAG_3 status registers.	Error output shutdown and latched	High-Z	Half-bridge control bits remain set despite error, however the output stage is shutdown. Clear EF to reactivate output stage.
Open load	Latch	1. Load Error bit, LE (bit 6) in SYS_DIAG 1: Global Status 1 Register 2. Localized error for each HS and LS channel of half-bridge, HBn_HS_OL and HBn_LS_OL bits in SYS_DIAG_5, SYS_DIAG_6 status registers.	None	No state change	An open load detection does not change the state of the output. EF to be cleared.
Temperature pre-warning	Latch	Global error bit 1, TPW in SYS_DIAG_1: Global Status 1 register	None	No state change	Not applicable
Temperature shutdown	Latch	Global error bit 2, TSD in SYS_DIAG_1: Global Status 1 register	All outputs shutdown and latched.	High-Z	Half-bridge control bits remain set despite error, however the output stage is shutdown. Clear EF to reactivate output stage.

Table 7 Summary of diagnosis and monitoring of outputs

TLE94108EL

Half-Bridge Outputs

Table 7 Summary of diagnosis and monitoring of outputs (cont'd)

6.2.1 Short Circuit of Output to Supply or Ground

The high-side switches are protected against short to ground whereas the low-side switches are protected against short to supply.

The high-side and low-side power switches will enter into an over-current condition if the current within the switch exceeds the overcurrent shutdown detection threshold, *I*_{SD}. Upon detection of the *I*_{SD} threshold, an overcurrent shutdown filter, t_{dSD} is begun. As the current rises beyond the threshold *I_{SD}*, it will be limited by the current limit threshold, *I*_{LIM}. Upon expiry of the overcurrent shutdown filter time, the affected power switch is latched off and the corresponding error bit, HBn_HS_OC or HBn_LS_OC is set and latched. See **[Figure 7](#page-30-3)** and **[Figure 8](#page-30-4)** for more detail. A global load error bit, LE, contained in the global status register, SYS_DIAG_1, is also set for ease of error scanning by the application software. The power switch remains deactivated as long as the error bit is set.

To resume normal functionality of the power switch (in the event the overcurrent condition disappears or to verify if the failure still exists) the microcontroller shall clear the error bit in the respective status register to reactivate the desired power switch.

Figure 7 High-Side Switch - Short Circuit and Overcurrent Protection

Table 8 Control and Status register bit state in the event of an overcurrent condition for an

6.2.2 Cross-Current

In bridge configurations the high-side and low-side power transistors are ensured never to be simultaneously "ON" to avoid cross currents. This is achieved by integrating delays in the driver stage of the power outputs to create a dead-time between switching off of one power transistor and switching on of the adjacent power transistor within the half-bridge. The dead times, t_{DHL} and t_{DLH} , as shown in [Figure 9](#page-32-2) case 3 and [Figure 10](#page-33-1) case 3, have been specified to ensure that the switching slopes do not overlap with each other. This prevents a cross conduction event.

TLE94108EL

Half-Bridge Outputs

Figure 10 Half bridge outputs switching times- low-side to high-side transition

6.2.3 Temperature Monitoring

Temperature sensors are integrated in the power stages. The temperature monitoring circuit compares the measured temperature to the warning and shutdown thresholds. If one or more temperature sensors reach the warning temperature, the temperature pre-warning bit, TPW is set. This bit is latched and can only be cleared via SPI. The outputs stages however remain activated.

If one or more temperature sensors reach the shut-down temperature threshold, **all outputs are latched off**. The TSD bit in SYS_DIAG_1: Global Status 1 is set. All outputs remain deactivated until the TSD bit is cleared. See **[Figure 11](#page-34-2)**.

To resume normal functionality of the power switch (in the event the overtemperature condition disappears, or to verify if the failure still exists) the microcontroller shall clear the TSD error bit in the status register to reactivate the respective power switch.

Figure 11 Overtemperature Behavior

Table 9 Control and Status register bit state in the event of an overtemperature condition for an activated power switch

6.2.4 Overvoltage and undervoltage shutdown

The power supply rails V_S and V_{DD} are monitored for supply fluctuations. The V_S supply is monitored for underand over-voltage conditions where as the V_{DD} supply is monitored for under-voltage conditions.

6.2.4.1 V_s Undervoltage

In the event the supply voltage V_s drops below the switch off voltage V_{UVOFE} , all output stages are switched off, however, the logic information remains intact and uncorrupted. The V_S under-voltage error bit, VS_UV, located in SYS_DIAG_1: Global Status 1 status register, will be set and latched. If *V_S* rises again and reaches the switch on voltage $V_{UV \, ON}$ threshold, the power stages will automatically be activated. The VS_UV error bit should be cleared to verify if the supply disruption is still present. See **[Figure 12](#page-36-1)**.

6.2.4.2 *V*_S Overvoltage

In the event the supply voltage V_S rises above the switch off voltage V_{ovOFF} , all output stages are switched off. The *V_S* over-voltage error bit, VS_OV, located in SYS_DIAG_1: Global Status 1 status register, will be set and latched. If V_S falls again and reaches the switch on voltage V_{OV ON} threshold, the power stages will automatically be activated. The VS_OV error bit should be cleared to verify if the overvoltage condition is still present. See **[Figure 12](#page-36-1)**.

6.2.4.3 *V*_{DD} Undervoltage

In the event the VDD logic supply decreases below the undervoltage threshold, $V_{DD\,POffR}$, the SPI interface shall no longer be functional and the TLE94108EL will enter reset.

The digital block will be initialized and the output stages are switched off to High impedance. The undervoltage reset is released once V_{DD} voltage levels are above the undervoltage threshold, $V_{DD\,POR}$.

The reset event is reported in SYS_DIAG1 by the NPOR bit (NPOR = 0) once the TLE94108EL is in normal mode $(EN = High; VDD > V_{DD POR}).$
TLE94108EL

Half-Bridge Outputs

Figure 12 Output behavior during under- and overvoltage V_s condition

6.2.5 Open Load

Both high-side and low-side switches of the half-bridge power outputs are capable of detecting an open load in their activated state. If a load current lower than the open load detection threshold, I_{OLD} for at least t_{dOLD} is detected at the activated switch, the corresponding error bit, HBn_HS_OL or HBn_LS_OL is set and latched. A global load error bit, LE, in the global status register, SYS_DIAG_1: Global Status 1, is also set for ease of error scanning by the application software. The half-bridge output however, remains activated.

The microcontroller must clear the error bit in the respective status register to determine if the open load is still present or disappeared.

High-side outputs, HS1 and HS2, are specifically designed to detect open load thresholds for LED loads. Both HS1 and HS2 have a unique and lower open load current threshold and filter time which are configurable via SPI in control register, FW_OL_CTRL.

During PWM operation, the open load detection is blanked and will not be visible in the status register for power stages used in active free-wheeling

7 Serial Peripheral Interface (SPI)

The TLE94108EL has a 16-bit SPI interface for output control and diagnostics. This section describes the SPI protocol, the control and status registers.

7.1 SPI Description

The 16-bit wide Control Input Word is read via the data input SDI, which is synchronized with the clock input SCLK provided by the microcontroller. SCLK must be Low during CSN falling edge (Clock Polarity = 0). The SPI incorporates an in-frame response: the content of the addressed register is shifted out at SDO within the same SPI frame (see **[Figure 19](#page-43-0)** and **[Figure 21](#page-45-0)**).The transmission cycle begins when the chip is selected by the input CSN (Chip Select Not), Low active. After the CSN input returns from Low to High, the word that has been read is interpreted according to the content. The SDO output switches to tri-state status (High impedance) at this point, thereby releasing the SDO bus for other use.The state of SDI is shifted into the input register with every falling edge on SCLK. The state of SDO is shifted out of the output register at every rising edge on SCLK (Clock Phase = 1). The SPI protocol of the TLE94108EL is compatible with independent slave configuration and with daisy chain. Daisy chaining is applicable to SPI devices with the same protocol.

Writing, clearing and reading is done byte wise. The SPI configuration and status bits are not cleared automatically by the device and therefore must be cleared by the microcontroller, e.g. if the TSD bit was set due to over temperature (refer to the respective register description for detailed information).

Figure 13 SPI Data Transfer Timing (note the reversed order of LSB and MSB as shown in this figure compared to the register description)

SPI messages are only recognized if a minimum set time, tSET, is observed upon rising edge of the EN pin (**[Figure 14](#page-38-0)**).

Figure 14 Setup time from EN rising edge to first SPI communication

Figure 15 SPI Data Timing

7.1.1 Global Error Flag

A logic OR combination between Global Error Flag (GEF) and the signal present on SDI is reported on SDO between a CSN falling edge and the first SCLK rising edge (**[Figure 13](#page-37-0)**). GEF is set if a fault condition is detected or if the device comes from a Power On Reset (POR).

Note: The SDI pin of all devices in daisy chain or non daisy chain mode must be Low at the beginning of the SPI frame (between the CSN falling edge and the first SCLK rising edge).

It is possible to check if the TLE94108EL has detected a fault by reading the GEF without SPI clock pulse (**[Figure 16](#page-39-0)**).

Figure 16 SDO behaviour with 0-clock cycle

7.1.2 Global Status Register

The SDO shifts out during the first eight SCLK cycles the Global Status Register. This register provides an overview of the device status. All failures conditions are reported in this byte:

- SPI protocol error (SPI_ERR)
- Load Error (LE bit): logical OR between Open Load (OL) and Overcurrent (OC) failures
- VS Undervoltage (VS_UV bit)
- VS Overvoltage (VS_OV bit)
- Negated Power ON Reset (NPOR bit)
- Temperature Shutdown (TSD bit)
- Temperature Pre-Warning (TPW bit)

See **[Chapter 7.7.1](#page-63-0)** for details.

Note: The Global Error Flag is a logic OR combination of every bit of the Global Status Register with the exception of NPOR: GEF = (SPI_ERR) OR (LE) OR (VS_UV) OR (VS_OV) OR (NOT(NPOR)) OR (TSD) OR (TPW).

The following table shows how failures are reported in the Global Status Register and by the Global Error Flag.

Table 10 Failure reported in the Global Status Register and Global Error Flag

Note: The default value (after Power ON Reset) of NPOR is 0, therefore the default value of GEF is 1.

7.1.3 SPI protocol error detection

The SPI incorporates an error flag in the Global Status Register (SPI_ERR, Bit7) to supervise and preserve the data integrity. If an SPI protocol error is detected during a given frame, the SPI_ERR bit is set in the next SPI communication.

The SPI_ERR bit is set in the following error conditions:

- the number of SCLK clock pulses received when CSN is Low is not 0, or is not a multiple of 8 and at least 16
- the microcontroller sends an SPI command to an unused address. In particular, SDI stuck to High is reported in the SPI_ERR bit
- the LSB of an address byte is not set to 1. In particular, SDI stuck to Low is reported in the SPI_ERR bit
- the Last Address Bit Token (LABT, bit 1 of the address byte, see **[Chapter 7.2](#page-42-0)**) in independent slave configuration is not set to 1
- the LABT bit of the last address byte in daisy chain configuration is not set to 1 (see **[Chapter 7.3](#page-44-0)**)
- a clock polarity error is detected (see **[Figure 17](#page-41-0)** Case 2 and Case 3): the incoming clock signal was High during CSN rising or falling edges.

For a correct SPI communication:

- SCLK must be Low for a minimum t_{BFF} before CSN falling edge and t_{lead} after CSN falling edge
- SCLK must be Low for a minimum t_{lag} before CSN rising edge and t_{BEH} after CSN rising edge

Figure 17 Clock Polarity Error

7.2 SPI with independent slave configuration

In an independent slave configuration, the microcontroller controls the CSN of each slave individually (**[Figure 18](#page-42-1)**).

Figure 18 SPI with independent slave configuration

Each SPI communication starts with one address byte followed by one data byte (**[Figure 19](#page-43-0)**).The LSB of the data byte must be set to '1'.The address bytes specifies:

- the type of operation: READ ONLY (OP bit =0) or READ/ WRITE (OP bit = 1) of the configuration bits, and READ ONLY (OP bit =0)or READ & CLEAR (OP bit = 1) of the status bits.
- The target register address (A[6:2])

The Last Address Byte Token bit (LABT, Bit1 of the address byte) must be set to 1, as no daisy chain configuration is used.

While the microcontroller sends the address byte on SDI, SDO shifts out GEF and the Global Status Register.

A further data byte (Bit15...8) is allocated to either configure the half-bridges or retrieve status information of the TLE94108EL.

Figure 19 SPI Operation Mode with independent slave configuration

The in-frame response characteristic enables the microcontroller to read the contents of the addressed register within the SPI command. See **[Figure 19](#page-43-0)**.

7.3 Daisy chain operation

The TLE94108EL supports daisy chain operation with devices with the same SPI protocol.This section describes the daisy chain hardware configuration with three devices from the TLE941xy family (See **[Figure 20](#page-45-1)**).

The master output (noted MO) is connected to a slave SDI and the first slave SDO is connected to the next slave SDI to form a chain. The SDO of the final slave in the chain will be connected to the master input (MI) to close the loop of the SPI communication frame. In daisy chain configuration, a single chip select, CSN, and clock signal, SCLK, connected in parallel to each slave device, are used by the microcontroller to control or access the SPI devices.

In this configuration, the Master Output must send the address bytes and data bytes in the following order:

- All address bytes must be sent first:
	- Address Byte 1 (for TLE941xy_1) is sent first, followed by Address Byte 2 (for TLE941xy_2) etc,...
	- The LABT bit of the last address byte must be 1, while the LABT bit of all the other address bytes must be 0
- The data bytes are sent all together once all address bytes have been transmitted: Data Byte 1 (for TLE941xy_1) is sent first, followed by Data Byte 2 (for TLE941xy_2) etc,...

The Master Input (MI), which is connected to the SDO of the last device in the daisy chain receives:

- A logic OR combination of all Global Error Flags (GEF), at the beginning of the SPI frame, between CSN falling edge and the first SCLK rising edge
- The logic OR combination of the GEFs is followed by the Global Status Registers in reverse order. In other words MI receives first the Global Status Register of the last device of the daisy chain
- Once all Global Status Registers are received, MI receives the response bytes corresponding to the respective address and data bytes in reverse order. For example, if the daisy chain consists of three devices with SDO or TLE941xy_3 connected to MI, the master receives first the Response Byte 3 of TLE941xy_3 (corresponding to Address Byte 3 and Data Byte 3) followed by the Response Byte 2 of TLE941xy_2 and finally the Response Byte 1 of TLE941xy_1.

An example of an SPI frame with three devices from the TLE941xy family is shown in **[Figure 21](#page-45-0)**.

Note: The signal on the SDI pin of the first IC in daisy chain (and in non-daisy chain mode), must be Low at the beginning of the SPI frame (between CSN falling edge and the first SCLK rising edge). This is because each Global Error Flag in daisy chain operation is implemented in OR logic.

Figure 20 Example of daisy chain hardware configuration with devices from the TLE941xy family

Figure 21 SPI frame with three devices of the TLE941xy family

Like in the individual slave configuration, it is possible to check if one or several TLE941xy have detected a fault condition by reading the logic OR combination of all the Global Error Flags when CSN goes Low without any clock cycle (**[Figure 22](#page-46-0)**).

Figure 22 Global Error Flag with zero SCLK clock cycle in daisy chain consisting only of TLE941xy devices

Note: Some SPI protocol errors such as the LSB of an address byte is wrongly equal to 0, may be reported in the SPI_ERR bit of another device in the daisy chain (refer to [Chapter 7.1.3](#page-40-0) and *[Chapter 7.7](#page-62-0)* for *more details on SPI_ERR). In this case some devices might accept wrong data during the corrupted SPI frame. Therefore if one of the devices in the daisy chain reports an SPI error, it is recommended to verify the content of the registers of all devices.*

7.4 Status register change during SPI communication

If a new failure occurs after the transfer of the data byte(s), i.e. between the end of the last address byte and the CSN rising edge, this failure will be reported in the next SPI frame (see example in **[Figure 23](#page-46-1)**).

Figure 23 Status register change during transfer of data byte - Example in independent slave configuration

No information is lost, even if a status register is changed during a SPI frame, in particular during a Read and Clear command. For example:

- the microcontroller sends a Read and Clear command to a status register
- the TLE94108EL detects during the transfer the data byte(s) a new fault condition, which is normally reported in the target status register

The incoming Clear command will be ignored, so that the microcontroller can read the new failure in the subsequent SPI frames.

Data inconsistency between the Global Status Register (see **[Chapter 7.7](#page-62-0)**) and the data byte (status register) within the same SPI frame is possible if:

- an open load or overcurrent error is detected during the transfer of the data byte
- the target status register corresponds to the new detected failure

In this case the new failure:

- is not reported in the Global Status Register of the current SPI frame but in the next one
- is reported in the data byte of the current SPI frame

Refer to **[Figure 23](#page-46-1)**.

Figure 24 Example of inconsistency between Global Error Flag and Status Register when a status bit is changed during the transfer of an address byte

7.5 SPI Bit Mapping

The SPI Registers have been mapped as shown in **[Figure 25](#page-49-0)** and **[Figure 26](#page-50-0)** respectively.

The control registers are READ/ WRITE registers. To set the control register to READ, bit 7 of the address byte (OP bit) must be programmed to '0', otherwise '1' for WRITE.

The status registers are READ/CLEAR registers. To CLEAR any Status Register, bit 7 of the address byte must be set to '1', otherwise '0' for READ.

Figure 25 TLE94108EL SPI Register mapping

Note: LABT: Last Address Bit Token, refer to [Chapter 7.2](#page-42-0) and [Chapter 7.3.](#page-44-0)

TLE94108EL

Figure 26 TLE94108EL Bit Mapping

7.6 SPI Control Registers

The Control Registers have a READ/WRITE access (see **[Chapter 7.5](#page-49-1)**):

- The 'POR' value is defined by the register content after a POR or device Reset
	- The default value of all control registers is 0000 0000_B with the exception of CONFIG_CTRL
	- The default value of the CONFIG_CTRL register is 0000 0010 $_B$
- One 16-bit SPI command consists of two bytes (see **[Figure 25](#page-49-0)** and **[Figure 26](#page-50-0)**), i.e.
	- an address byte
	- followed by a data byte
- The control bits are not cleared or changed automatically by the device. This must be done by the microcontroller via SPI programming.
- Reading a register is done byte wise by setting the SPI bit 7 to "0" (= READ ONLY).
- Writing to a register is done byte wise by setting the SPI bit 7 to "1".

7.6.1 Control register definition

HB_ACT_1_CTRL

Half-bridge output control 1 (Address Byte [OP] 000 00[LABT]1_B)

Note: The simultaneous activation of both HS and LS switch within a half-bridge is prevented by the digital block to avoid cross current. If both LS_EN and HS_EN bits of a given half-bridge are set, the logic turns off this half-bridge.

HB_ACT_2_CTRL

Half-bridge output control 2 (Address Byte [OP]100 00[LABT]1_B)

Note: The simultaneous activation of both HS and LS switch within a half-bridge is prevented by the digital block to avoid cross current. If both LS_EN and HS_EN bits of a given half-bridge are set, the logic turns off this half-bridge.

HB_MODE_1_CTRL Half-bridge output mode control 1 (Address Byte [OP]110 00[LABT]1_B)

HB_MODE_2_CTRL Half-bridge output mode control 2 (Address Byte [OP]001 00[LABT]1_B)

PWM_CH_FREQ_CTRL PWM channel frequency select (Address Byte [OP]011 00[LABT]1_B)

1) Not subject to production test, guaranteed by design. Frequency may deviate by $\pm 10\%$

PWM1_DC_CTRL PWM channel 1 duty cycle configuration (Address Byte [OP]111 00[LABT]1_B)

Note: Refer to [Chapter 6.1.1](#page-24-0) for more information on PWM operation

PWM2_DC_CTRL PWM channel 2 duty cycle configuration (Address [OP]000 10[LABT]1_B)

PWM3_DC_CTRL PWM channel 3 duty cycle configuration (Address Byte [OP]100 10[LABT]1_B)

FW_OL_CTRL

Free-wheeling configuration and Open load detection setting of HS1 and HS2 (Address Byte [OP]010 10[LABT]1_B)

FW_CTRL

Free-wheeling configuration (Address Byte [OP]110 10[LABT]1)_B

CONFIG_CTRL

Device Configuration control (Address Byte [OP]110 01[LABT]1_B)

7.7 SPI Status Registers

The Control Registers have a READ/CLEAR access (see also **[Chapter 7.5](#page-49-1)**):

- The 'POR Value' of the Status registers (content after a POR or device Reset) and is 0000 0000_B.
- One 16-bit SPI command consists of two bytes (see **[Figure 25](#page-49-0)** and **[Figure 26](#page-50-0)**), i.e.
	- an address byte
	- followed by a data byte
- Reading a register is done byte wise by setting the SPI bit 7 of the address byte to "0" (= Read Only).
- Clearing a register is done byte wise by setting the SPI bit 7 of the address byte to "1".
- SPI status registers are not cleared automatically by the device. This must be done by the microcontroller via SPI command.

7.7.1 Status register definition

SYS_DIAG1

Global status 1 (Address Byte [OP]001 10[LABT]1_B)

Note: The LE bit in the Global Status register is read only. It reflects an OR combination of the respective open load and overcurrent errors of the half-bridge channels. If all OC/ OL bits of the respective highside and low-side channels are cleared to '0', the LE bit will be automatically updated to '0'.

SYS_DIAG_2 : OP_ERROR_1_STAT Overcurrent error status of half-bridge outputs 1 - 4 (Address Byte [OP]101 10[LABT]1_B)

SYS_DIAG_3 : OP_ERROR_2_STAT Overcurrent error status of half-bridge outputs 5 - 8 (Address Byte [OP]011 10[LABT]1_B)

SYS_DIAG_5 : OP_ERROR_4_STAT Open load error status of half-bridge outputs 1 - 4 (Address Byte [OP]000 01[LABT]1_B)

SYS_DIAG_6 : OP_ERROR_5_STAT Open load error status of half-bridge outputs 5 - 8 (Address Byte [OP]100 01[LABT]1_B)

Application Information

8 Application Information

Note: The following simplified application examples are given as a hint for the implementation of the device only and shall not be regarded as a description or warranty of a certain functionality, condition or quality of the device. The function of the described circuits must be verified in the real application.

8.1 Application Diagram

Figure 27 Application example for DC-motor loads

TLE94108EL

Application Information

Figure 28 Application example for side mirror control

Notes on the application example

- *1. Series resistors between the microcontroller and the signal pins of the TLE94108EL are recommended if an active reverse polarity protection (MOSFET) is used to protect VS1 and VS2 pins. These resistors limit the current between the microcontroller and the device during negative transients on VBAT (e.g. ISO/TR 7637 pulse 1)*
- *2. Landing pads for ceramic capacitors at the outputs of the TLE94108EL as close as possible to the connectors are recommended (the ceramic capacitors are not populated if unused). These ceramic capacitors can be mounted if a higher performance in term of ESD capability is required.*
- *3. The electrolytic capacitor at the VSx pins should be dimensioned in order to prevent the VS voltage from exceeding the absolute maximum rating. PWM operation with a too low capacitance can lead to a VS voltage overshoot, which results in a VS overvoltage detection.*

Application Information

- *4. Not used (NU) pins and unused outputs are recommended to be left unconnected (open) in the application. If NU pins or unused output pins are routed to an external connector which leaves the PCB, then these outputs should have provision for a zero ohm jumper (depopulated if unused) or ESD protection. In other words, NU and unused pins should be treated like used pins.*
- *5. Place bypass ceramic capacitors as close as possible to the VSx pins, with shortest connections the GND pins and GND layer, for best EMC performance*

TLE94108EL

Application Information

8.2 Thermal application information

Ta = -40°C, Ch1 to Ch8 are dissipating a total of 1.6W (0.2W each). Ta = 85°C, Ch1 to Ch8 are dissipating a total of 1.08W (0.135W each).

Figure 29 ZthJA Curve for different PCB setups

Figure 30 ZthJC Curve

Application Information

8.3 EMC Enhancement

In the event the emissions of the device exceed the allowable limits, a modulation of the oscillator frequency is incorporated to reduce eventual harmonics of the 8MHz base clock. The frequencies can be selected based on the resolution bandwidth of the peak detector during EMC testing.

The selection is achieved by setting the FM_CLK_MODn bits in the PWM_CH_FREQ_CTRL register as follows:

 00_B : OFF 01_B : FM CLK=15.625 kHZ 10_B: FM CLK=31.25 kHz 11_B : FM CLK=62.5 kHz

Package Outlines

Figure 31 PG-SSOP-24 (Plastic/Plastic Green - Dual Small Outline Package)

Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e lead-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

For further information on alternative packages, please visit our website: **http://www.infineon.com/packages**. Dimensions in mm

Revision History

10 Revision History

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